



I8216/I8226 **4-BIT PARALLEL BIDIRECTIONAL BUS DRIVER** *INDUSTRIAL*

- Data Bus Buffer Driver
- Low Input Load Current — .25 mA Maximum
- High Output Drive Capability for Driving System Data Bus
- 3.65V Output High Voltage
- Three State Outputs
- Reduces System Package Count
- Industrial Temperature Range: -40° to $+85^{\circ}\text{C}$

The I8216/I8226 is a 4-bit bidirectional bus driver/receiver.

All inputs are low power TTL compatible. For driving MOS, the DO outputs provide a high 3.65V V_{OH} , and for high capacitance terminated bus structures, the DB outputs provide a high 50mA I_{OL} capability.

A non-inverting (I8216) and an inverting (I8226) are available to meet a wide variety of applications for buffering in microcomputer systems.

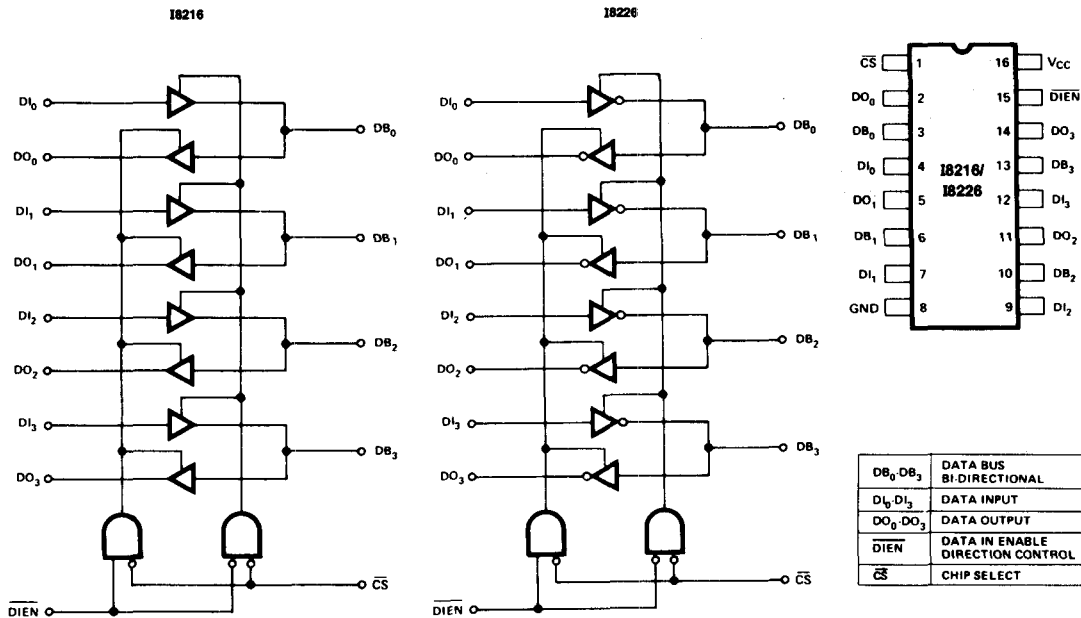


Figure 1. Logic Diagrams

Figure 2. Pin Configuration

ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias - 40°C to 85°C
Storage Temperature - 65°C to + 150°C
All Output and Supply Voltages - 0.5V to + 7V
All Input Voltages - 1.0V to + 5.5V
Output Currents 125 mA

**NOTICE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

D.C. CHARACTERISTICS (T_A = -40°C to 85°C, V_{CC} = +5V ±10%)

Symbol	Parameter	Limits			Unit	Conditions
		Min.	Typ.	Max.		
I _{F1}	Input Load Current D1EN, CS		-0.15	-.5	mA	V _F = 0.45
I _{F2}	Input Load Current All Other Inputs		-0.08	-.25	mA	V _F = 0.45
I _{R1}	Input Leakage Current D1EN, CS			20	μA	V _R = 5.25V
I _{R2}	Input Leakage Current DI Inputs			10	μA	V _R = 5.25V
V _C	Input Forward Voltage Clamp			-1	V	I _C = -5mA
V _{IL}	Input "Low" Voltage			.95	V	
V _{IH}	Input "High" Voltage	2.0			V	
I _{IO}	Output Leakage Current DO (3-State) DB			20 100	μA	V _O = 0.45V/5.25V
I _{CC}	Power Supply Current 8216		95	130	mA	
	8226		85	120	mA	
V _{OL1}	Output "Low" Voltage DO, DB Outputs		0.3	.45	V	DO Outputs I _{OL} = 15mA DB Outputs I _{OL} = 25mA
V _{OL2}	Output "Low" Voltage 8216 DB Outputs Only		0.5	.6	V	DB Outputs I _{OL} = 50mA
	8226		0.5	.6	V	DB Outputs I _{OL} = 45mA
V _{OH1}	Output "High" Voltage DO Outputs	3.65	4.0		V	DO Outputs I _{OH} = -1mA
V _{OH2}	Output "High" Voltage DB Outputs	2.4	3.0		V	DB Outputs I _{OH} = -10mA
I _{OS}	Output Short Circuit Current	-15	-35	-65	mA	DO Outputs V _O ≅ 0V,
		-30	-75	-120	mA	DB Outputs V _{CC} = 5.0V

NOTE: Typical values are for T_A = 25°C, V_{CC} = 5.0V.

CAPACITANCE (V_{BIAS} = 2.5V, V_{CC} = 5.0V, T_A = 25°C)

Symbol	Parameter	Limits			Unit
		Min.	Typ. ^[1]	Max.	
C _{IN}	Input Capacitance		4	8	pF
C _{OUT1}	Output Capacitance		6	10	pF
C _{OUT2}	Output Capacitance		13	20	pF

A.C. CHARACTERISTICS ($T_A = -40^{\circ}\text{C}$ to 85°C , $V_{CC} = +5\text{V} \pm 10\%$)

Symbol	Parameter	Limits			Unit	Conditions
		Min.	Typ. ^[1]	Max.		
T_{PD1}	Input to Output Delay DO Outputs		15	25	ns	$C_L = 30\text{pF}$, $R_1 = 300\Omega$ $R_2 = 600\Omega$
T_{PD2}	Input to Output Delay DB Outputs		20	30	ns	$C_L = 300\text{pF}$, $R_1 = 90\Omega$ $R_2 = 180\Omega$
	8216		16	25	ns	
T_E	Output Enable Time		45	65	ns	(Note 2)
	8216		36	54	ns	(Note 2)
T_D	Output Disable Time		20	35	ns	(Note 2)

NOTES:

1. Typical values are for $T_A = 25^{\circ}\text{C}$, $V_{CC} = 5.0\text{V}$.

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TEST	C_L	R_1	R_2
T_{PD1}	30 pF	300 Ω	600 Ω
T_{PD2}	300 pF	90 Ω	180 Ω
T_E (DO. ENABLE ⁽¹⁾)	30 pF	10K Ω	1K Ω
T_E (DO. ENABLE ⁽¹⁾)	30 pF	300 Ω	600 Ω
T_E (DB. ENABLE ⁽¹⁾)	300 pF	10K Ω	1K Ω
T_E (DB. ENABLE ⁽¹⁾)	300 pF	90 Ω	180 Ω
T_D (DO. DISABLE ⁽¹⁾)	5 pF	300 Ω	600 Ω
T_D (DO. DISABLE ⁽¹⁾)	5 pF	10K Ω	1K Ω
T_D (DB. DISABLE ⁽¹⁾)	5 pF	90 Ω	180 Ω
T_D (DB. DISABLE ⁽¹⁾)	5 pF	10K Ω	1K Ω

TEST CONDITIONS:

Input pulse amplitude of 2.5V.

Input rise and fall times of 5 ns between 1 and 2 volts.

Output loading is 5 mA and 10 pF.

Speed measurements are made at 1.5 volt levels.

A.C. TESTING LOAD CIRCUIT

